

MDL-XF-1160/1-5000mW



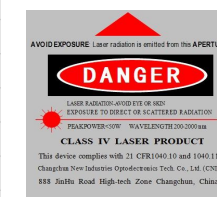
INFRARED DIODE LASER AT 1160nm

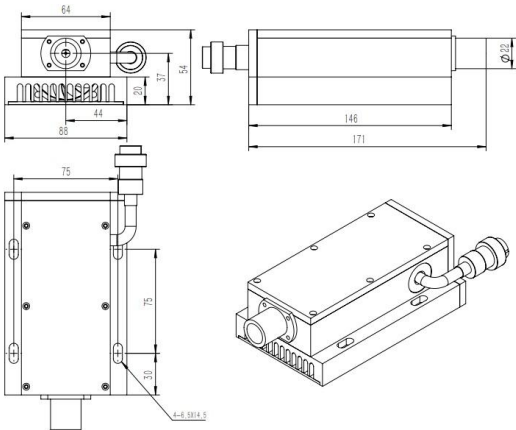
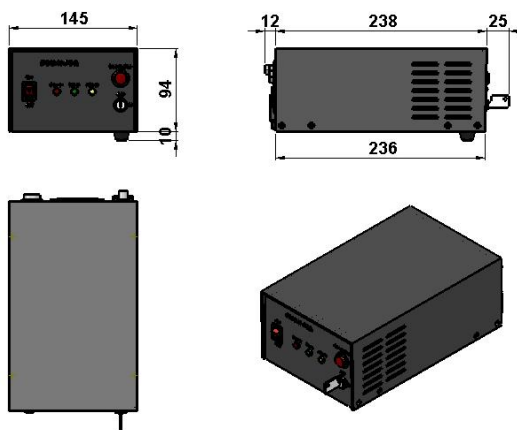
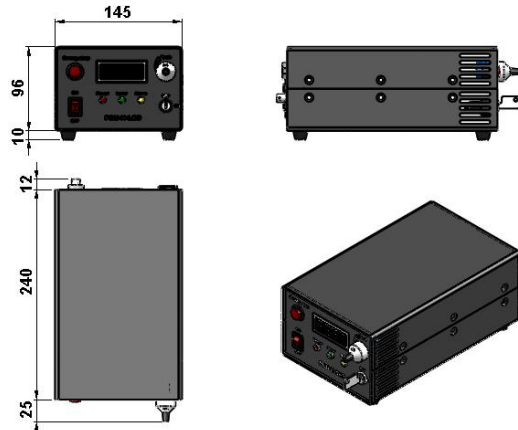
It features ultra compact design, long lifetime, cost-effectiveness and easy operation. They are widely used in measurement, communication, spectrum analysis, etc.



SPECIFICATIONS

Central wavelength (nm)	1160±5
Operating mode	CW
Output power (mW) ¹	1-5000
Power stability (rms, 4 hours ± 3°C)	<2%, <1%, <0.5%
Transverse mode	Multimode
Dimensions of beam at the aperture (mm)	~5×8
Beam divergence, full angle (mrad)	<3.0
Warm-up time (minutes)	<5
Cooled method	Air cooled
Beam height from base plate (mm)	37
Operating temperature (°C)	10-35
Power supply (100-240VAC)	PSU-H-FDA/PSU-H-LED
Modulation option	DC-1kHz, 1kHz-10kHz, 10kHz-30kHz optional; TTL and Analog optional
Expected lifetime (hours)	>10000



LASER HEAD	POWER SUPPLY (PSU-H-FDA) ²	POWER SUPPLY (PSU-H-LED) ³
 171 (L) × 88 (W) × 54 (H) mm³, 1.4kg	 275 (L) × 145 (W) × 104 (H) mm³, 2.1kg	 277 (L) × 145 (W) × 106 (H) mm³, 2.3kg

1 Any power level can be selected in this range.

2 Fixed output power; Modulation up to 30kHz.

3 Output power adjustable 10-100%; RS232 control optional; Modulation up to 30kHz.